

 Active

*L1: (2) ("5998016").PN.

L2: (2) "20020186582"

♥ L3: (5907) (438/3,104,238,239,241,672,692).CCLS

* L4. (15) (((magnetoresistive and trench) and insulat\$3 and magnetic and c

- L5: (119) 3 and magnetoresistive


L6: (24) ((438/3, 104, 238, 239, 241, 242, 386, 672, 692). CCLS.) and ((magne

L7: (5506) (257/295,296,421,422,903-908). CCLS

*L8. (15) ((257/295,296,421,422,903-908).CCLS.) and (magnetoresistive

^aL9 (24) ((438,3,104,238,239,241,242,257,386,672,692),CCLS) and (fn

Failed

 Saved

☛ (13063) magnetoresistive

(285) magnetoresistive and trench

(153) (magnetoresistive and trench) and insulat\$3 and magnetic and condu

(10) ((magnetoresistive and trench) and insulat\$3 and magnetic and cond

USPAT:US,PGPUB,EPC:JPG,DERM,F:Fluents

Default operator: OR

✦ Highlight all the terms initially

((438/3, 104, 238, 239, 241, 242, 257, 386, 672, 692) CCLS
) and ((magnetoresistive and trench) and insulat\$3 and
magnetic and conductive

大 藥 房

	U	I	Document ID	Issue Date	Pages	Title	Current	Current X	Re	Inventor	S	C
1	□	□	US 20040014243 A1	20040122	21	MAGNETORESISTIVE	438/3		43	Drewes, Joel A.	□	□
2	□	□	US 20030219980 A1	20031127	21	Pattern forming method,	438/687	438/672	43	Kamijima, Akifumi	□	□
3	□	□	US 20030215961 A1	20031120	20	Self-aligned, trenchless	438/3		43	Doan, Trung T. et al	□	□
4	□	□	US 20030207471 A1	20031106	20	Self-aligned, trenchless	438/3		43	Doan, Trung T. et al	□	□
5	□	□	US 20030203510 A1	20031030	18	Protective layers for MR	438/3	257/296	43	Hineman, Max et al	□	□
6	□	□	US 20030199167 A1	20031023	21	Control of MTJ tunnel ar	438/692		43	Tuttle, Mark E.	□	□
7	□	□	US 20030137028 A1	20030724	90	Semiconductor integrate	257/528	257/536,	43	Hosotani, Keiji et al	□	□
8	□	□	US 20020132375 A1	20020919	20	Self-aligned, trenchless	438/3		43	Doan, Trung T. et al	□	□
9	□	□	US 20010050859 A1	20011213	13	Memory cell array and m	365/158	257/295,	43	Schwarzl, Siegfried	□	□